

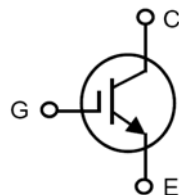
**High Voltage  
XPT™ IGBT**
**IXYA12N250CHV  
IXYH12N250CHV**

$$V_{CES} = 2500V$$

$$I_{C110} = 12A$$

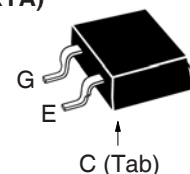
$$V_{CE(sat)} \leq 4.50V$$

$$t_{fi(typ)} = 136ns$$

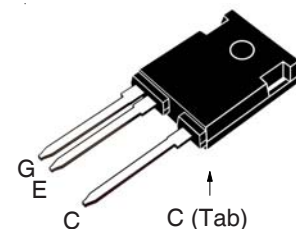


Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $175^\circ C$	2500	V
$V_{CGR}$	$T_J = 25^\circ C$ to $175^\circ C$ , $R_{GE} = 1M\Omega$	2500	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$	28	A
$I_{C110}$	$T_C = 110^\circ C$	12	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	80	A
<b>SSOA (RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 150^\circ C$ , $R_G = 10\Omega$ Clamped Inductive Load	$I_{CM} = 48$ 1500	A V
$P_C$	$T_C = 25^\circ C$	310	W
$T_J$		-55 ... +175	$^\circ C$
$T_{JM}$		175	$^\circ C$
$T_{stg}$		-55 ... +175	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
$M_d$	Mounting Torque (TO-247HV)	1.13/10	Nm/lb.in.
<b>Weight</b>	TO-263HV	2.5	g
	TO-247HV	6.0	g

TO-263HV (IXYA)



TO-247HV (IXYH)



G = Gate      C = Collector  
E = Emitter    Tab = Collector

**Features**

- High Voltage Packages
- High Blocking Voltage
- High Peak Current Capability
- Low Saturation Voltage

**Advantages**

- Low Gate Drive Requirement
- High Power Density

**Applications**

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	2500		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.0		5.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 150^\circ C$			10 $\mu A$ 3 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 12A$ , $V_{GE} = 15V$ , Note 1 $T_J = 150^\circ C$	3.70	5.55	V V



Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

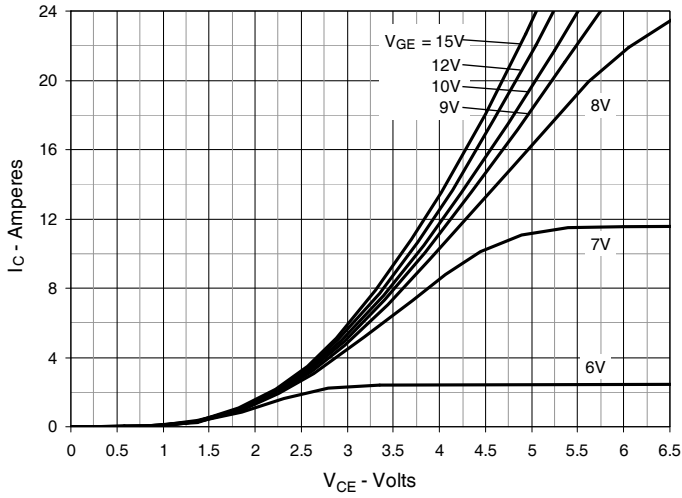


Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$

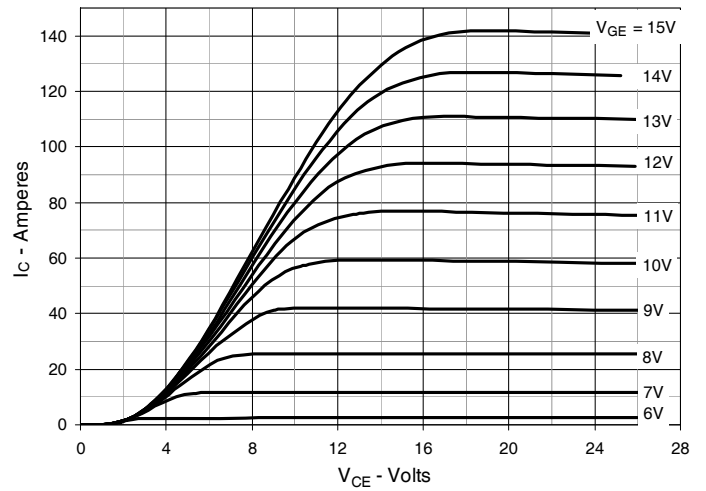


Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$

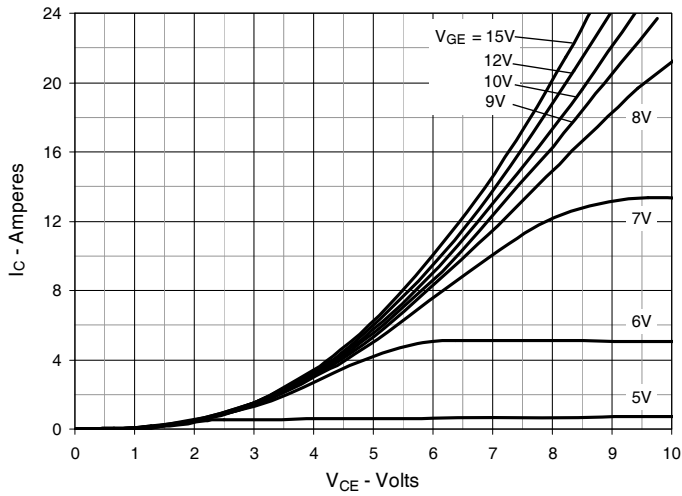


Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature

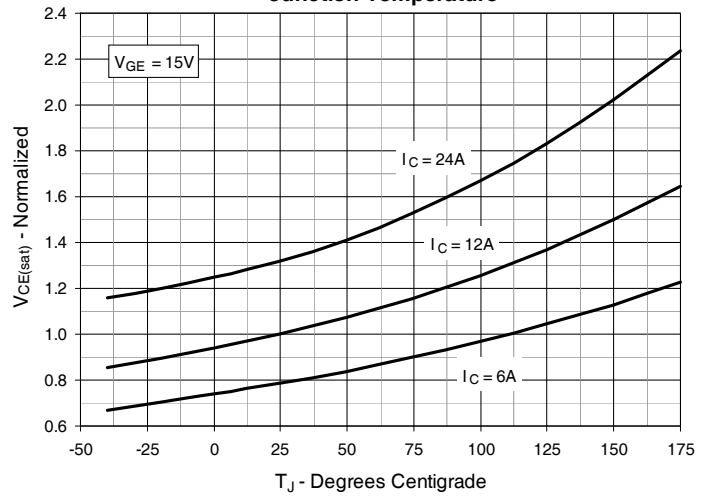


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

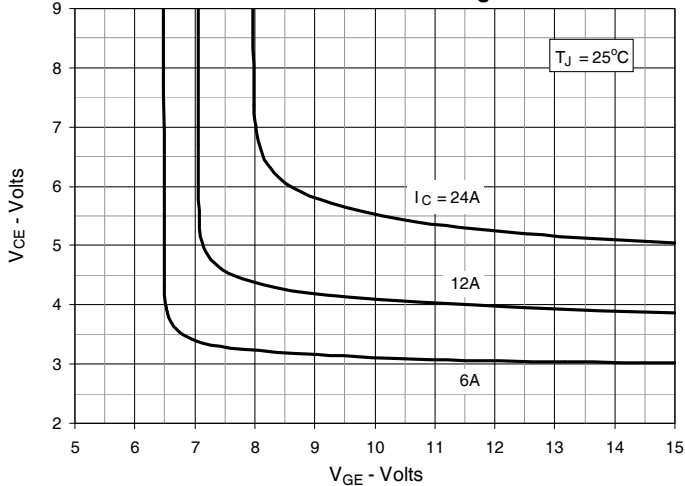
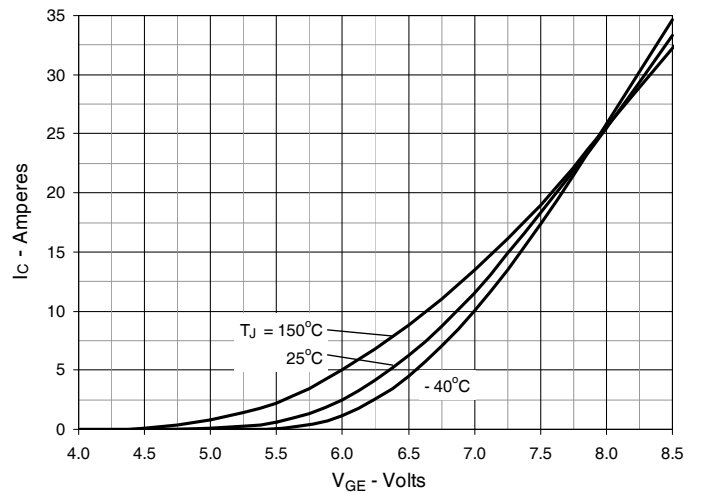
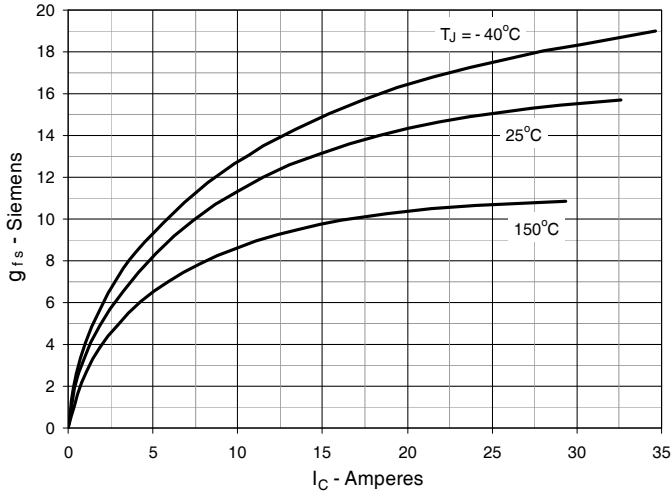


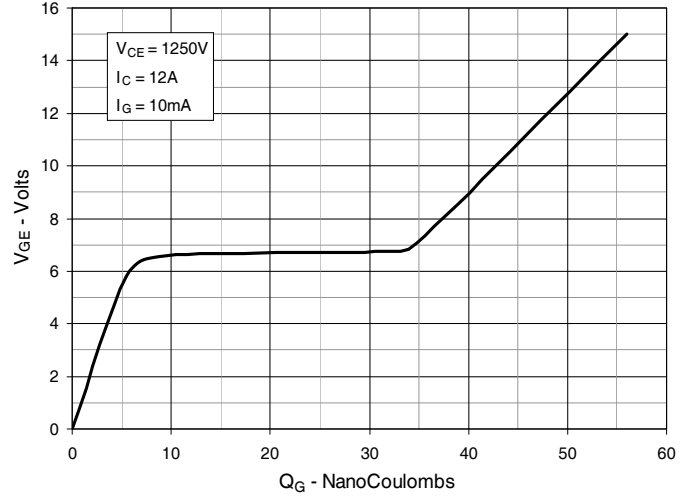
Fig. 6. Input Admittance



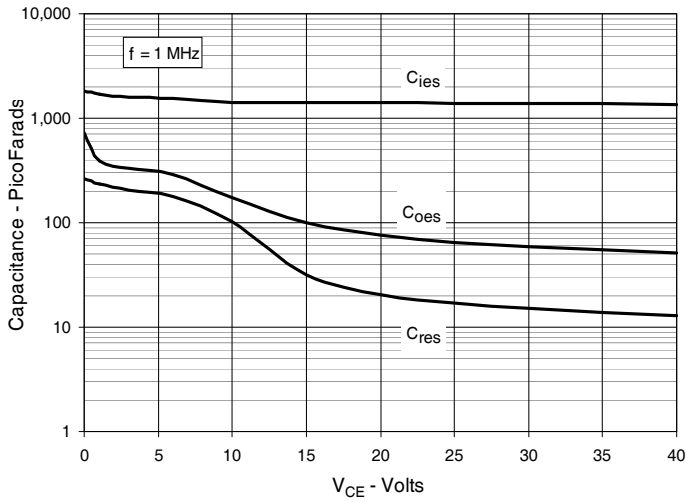
**Fig. 7. Transconductance**



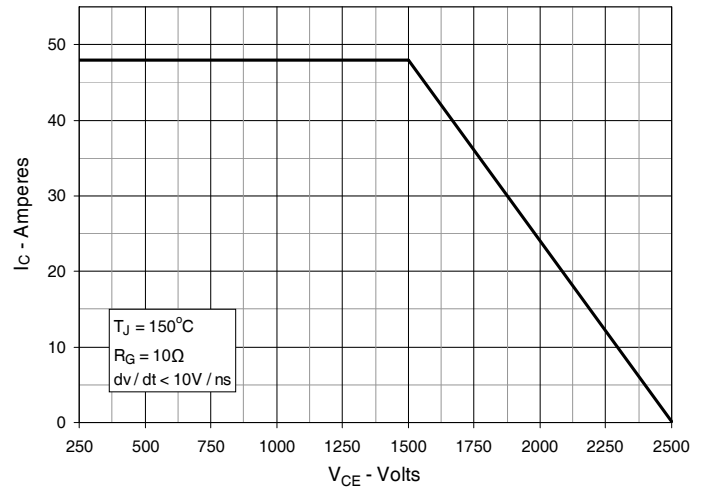
**Fig. 8. Gate Charge**



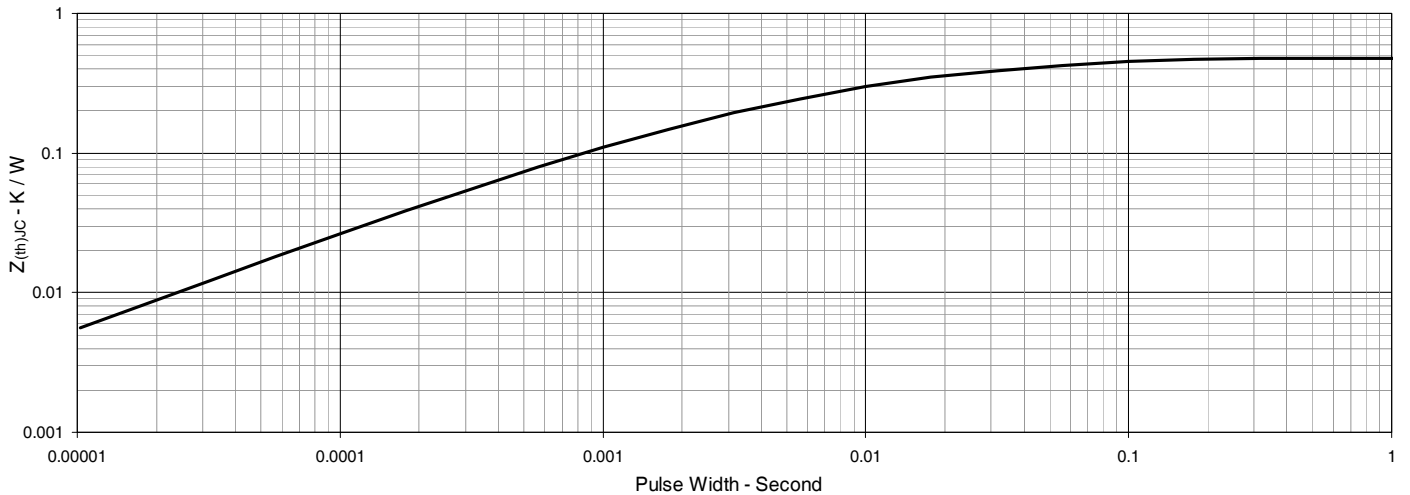
**Fig. 9. Capacitance**



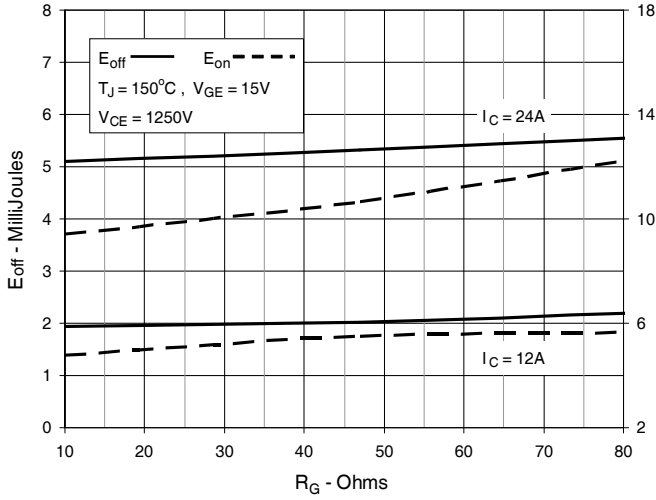
**Fig. 10. Reverse-Bias Safe Operating Area**



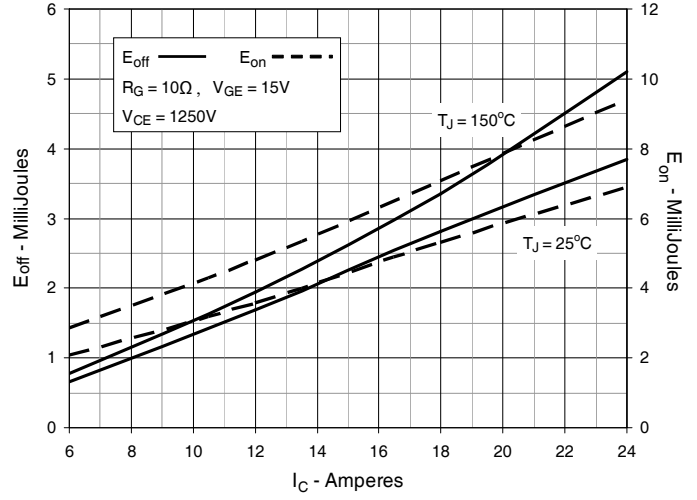
**Fig. 11. Maximum Transient Thermal Impedance**



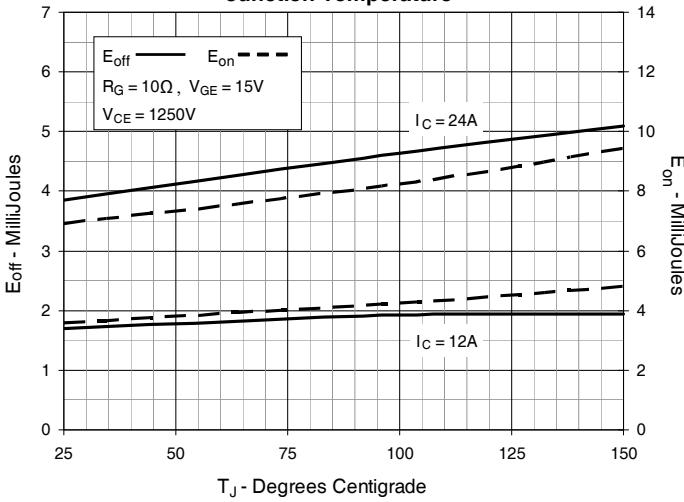
**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**



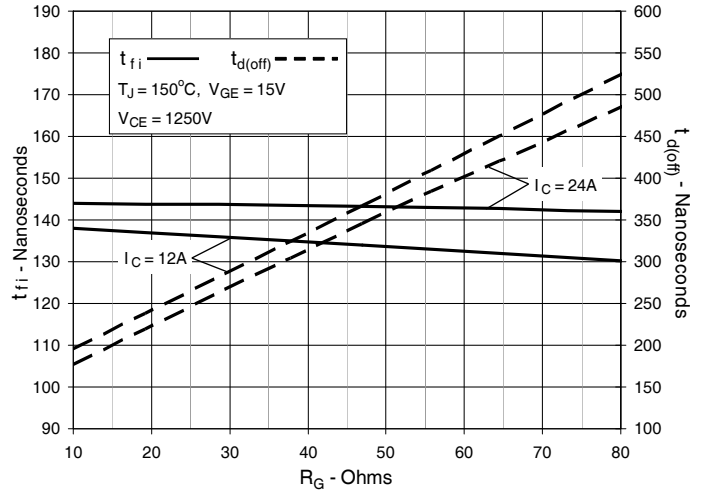
**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**



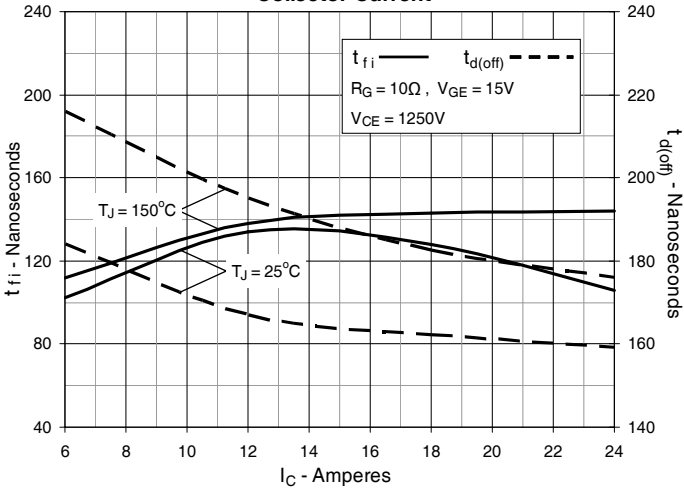
**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**



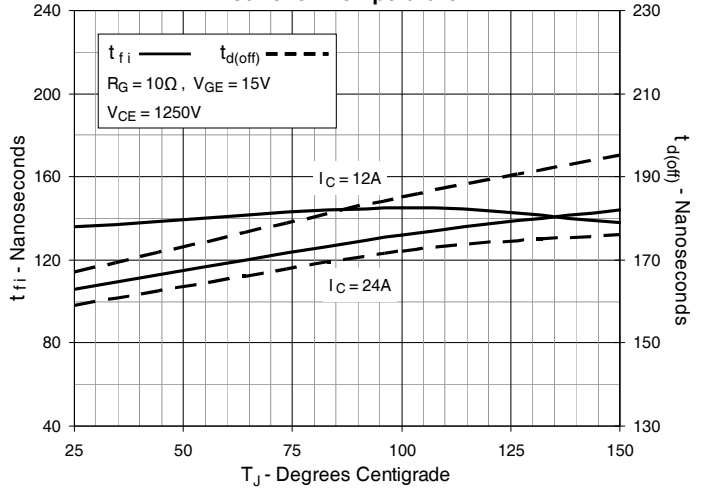
**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**



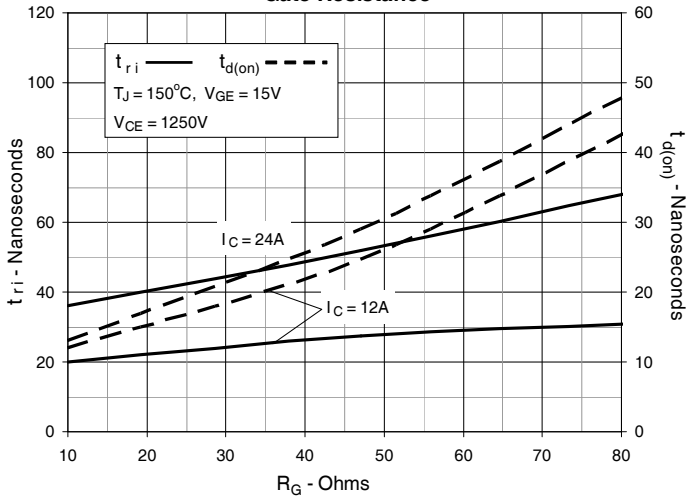
**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**



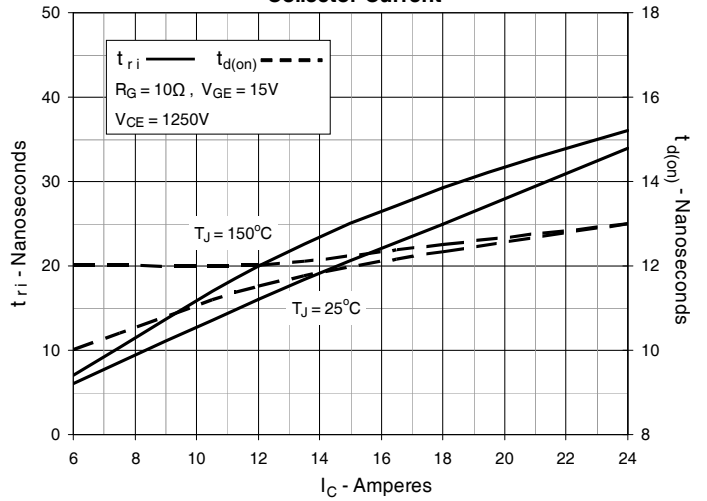
**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**



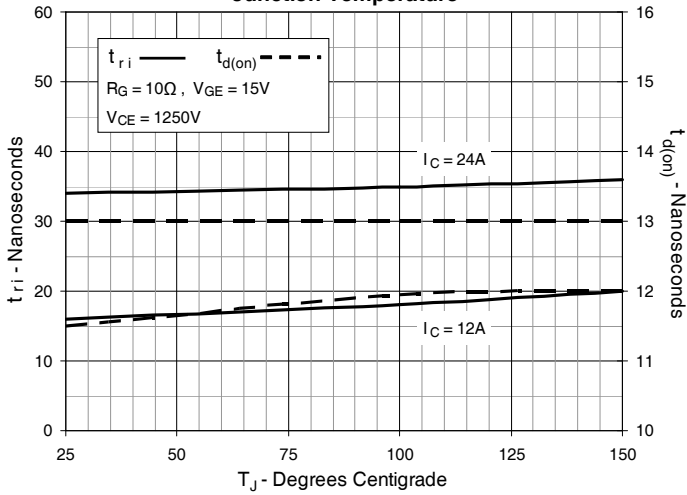
**Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature**





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